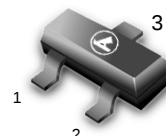


High Voltage Switching Diode



BAS21LT1



CASE 318-08, STYLE 8
SOT-23 (TO-236AB)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	250	Vdc
Peak Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	625	mAdc

DEVICE MARKING

BAS21LT1 = JS

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

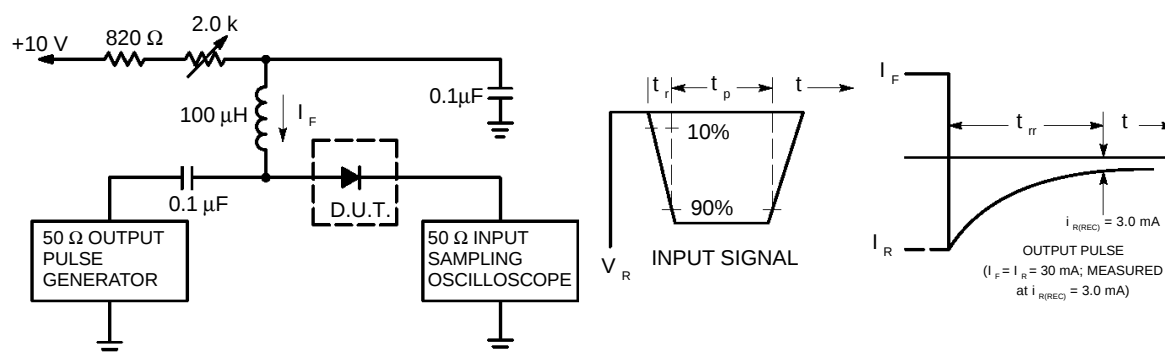
Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Reverse Voltage Leakage Current ($V_R = 200\text{Vdc}$)	I_R	—	1.0	μAdc
($V_R = 200\text{Vdc}$, $T_J = 150^\circ\text{C}$)		—	100	
Reverse Breakdown Voltage ($I_{BR} = 100 \mu\text{Adc}$)	$V_{(BR)}$	250	—	Vdc
Forward Voltage ($I_F = 100 \text{mAdc}$)	V_F	—	1000	mV
($I_F = 200 \text{mAdc}$)		—	1250	
Diode Capacitance ($V_R = 0$, $f = 1.0 \text{MHz}$)	C_D	—	5.0	pF
Reverse Recovery Time ($I_F = I_R = 30\text{mAdc}$, $R_L = 100 \Omega$)	t_{rr}	—	50	ns

1. FR-5 = $1.0 \times 0.75 \times 0.062 \text{ in.}$

2. Alumina = $0.4 \times 0.3 \times 0.024 \text{ in.}$ 99.5% alumina.

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- Notes:
1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit